AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method for producing a semiconductor device comprising:

forming a resist pattern to be used as a mask over a multi-layered film, wherein the multi-layered film includes a nitride etching stop film, a first organic insulating film, a first oxide etching stop film, a second organic insulating film, and a second oxide etching stop film layered in this order so that the second oxide etching stop film is formed between the resist pattern and the second organic insulating film to protect the second organic insulating film,

wherein the nitride etching stop film and the first and second oxide etching stop films are all provided as continuous layers with no apertures defined therein when the resist pattern is formed over the multi-layered film, [[and]]

forming an opening by an etching process using the resist pattern as a mask during at least a part of forming the opening, wherein the opening penetrates at least the first and second organic insulating films and is of substantially the same size in both the first and second organic insulating films, and

wherein the second oxide etching stop film is used as a mask when forming the opening in the first organic insulating film so that the second oxide etching stop film is

thinned but no aperture is formed therein during the forming of the opening in the first organic insulating film.

2. (Original) A method for producing a semiconductor device as claimed in claim 1, wherein the first organic insulating film has a dielectric constant of about 3 or lower.

3. (Original) A method for producing a semiconductor device as claimed in claim 1, wherein the first organic insulating film includes a single layer or a multi-layered film of polytetrafluoroethylene, fluorinated polyallyl ether or fluorinated polyimide.

4. (Original) A method for producing a semiconductor device as claimed in claim 3, wherein the second etching stop film is made from the same material as the first etching stop film.

5. (Original) A method for producing a semiconductor device as claimed in claim 1, wherein the first etching stop film is a film that functions as an etching stopper to the first organic insulating film and has an insulating function.

6. (Original) A method for producing a semiconductor device as claimed in claim 5, wherein the first etching stop film has a selectivity ratio with respect to the second organic insulating film of 5 or higher.

7. (Canceled)

8. (Original) A method for producing a semiconductor device as claimed in claim 1, wherein the second etching stop film is formed of such a material in such a film thickness that the second organic insulating film is protected from being etched when an opening is formed through the second organic insulating film to the first organic insulating film.

9. (Original) A method for producing a semiconductor device as claimed in claim 1, wherein another etching stop film which is functioned as a diffusion barrier for metallic elements or impurities is provided under the multi-layered film.

10-11. (Canceled)

12. (Previously presented) The method of claim 1, wherein another resist is used as a mask in enlarging the opening in the second organic insulating film but not the first organic insulating film.

13. (New) The method of claim 1, wherein the second etching stop film is thicker than the first etching stop film immediately after the first and second etching stop films

are deposited, so that during said forming of the opening in the first organic insulating film the first etching stop film is penetrated and removed in an area of the opening but the second etching stop film is thinned but no aperture is formed therein during said forming of the opening in the first organic insulating film.

14. (New) A method for producing a semiconductor device, the method comprising:

forming a resist pattern to be used as a mask over a multi-layered film, wherein the multi-layered film includes a nitride inclusive etching stop film, a first organic insulating film, a first etching stop film, a second organic insulating film, and a second etching stop film layered in this order so that the second etching stop film is formed between the resist pattern and the second organic insulating film to protect the second organic insulating film,

wherein the nitride inclusive etching stop film and the first and second etching stop films are all provided as continuous layers with no apertures defined therein when the resist pattern is originally formed over the multi-layered film,

forming an opening by an etching process using the resist pattern as a mask during at least a part of forming the opening, wherein the opening penetrates at least the first and second organic insulating films and is of substantially the same size in both the first and second organic insulating films, and

wherein the second etching stop film is used as a mask when forming the opening in the first organic insulating film so that the second etching stop film is thinned but no aperture is formed therein during the forming of the opening in the first organic insulating film.

15. (New) The method of claim 14, wherein the second etching stop film is thicker than the first etching stop film immediately after the first and second etching stop films are deposited, so that during said forming of the opening in the first organic insulating film the first etching stop film is penetrated and removed in an area of the opening but the second etching stop film is thinned but no aperture is formed therein during said forming of the opening in the first organic insulating film.